## **Supporting Information for:** Hysteresis and Its Impact on Characterizing Mechanical Properties of Suspended Monolayer Molybdenum-disulfide Films

Haosheng Pang,<sup>a</sup> Peng Huang,<sup>c</sup> Weirong Zhuo,<sup>a</sup> Minglin Li<sup>a,b,\*</sup>, Chenghui Gao<sup>a,\*</sup> and Dan Guo<sup>c,\*</sup>

<sup>a</sup>School of Mechanical Engineering and Automation, Fuzhou University, Fuzhou 350108, China <sup>b</sup>Fujian Key Laboratory of Medical Instrumentation and Pharmaceutical Technology, Fuzhou University, Fuzhou 350108, China <sup>c</sup>State Key Laboratory of Tribology, Tsinghua University, Beijing 100084, China \*The Correspondence should be addressed to liminglin@fzu.edu.cn, gch@fzu.edu.cn, and guodan26@tsinghua.edu.cn



Figure S1. Scanning electron micrograph of AFM tip (radius= about 30 nm) (a) before and (b) after use in our experiments. (a) is from the database of manufacturer (Olympus company).



Figure S2. The force-displacement curves for a square MoS<sub>2</sub> monolayers, with the side length of 1.5 µm and performed at the force of 1500 nN. 1<sup>th</sup>, 2<sup>th</sup>, 3<sup>th</sup>, 4<sup>th</sup>, and 5<sup>th</sup> mean the first, the second, the third, the fourth, and the fifth supplemental nanoindentation experiments.



Figure S3. Energy dissipations of hysteresis loops in monolayer MoS<sub>2</sub> sheets for 1<sup>th</sup> ~5<sup>th</sup> supplemental nanoindentation experiments.



Figure S4. Scanning electron micrograph of AFM tip (diameter= about 35 nm) after use in the supplemental nanoindentation experiments. The Scanning electron micrograph of AFM tip before the supplemental experiments is the same as Figure S1 (a).

## **MD** simultions

In the MD simulations, the monolayer  $MoS_2$  film is comprised of a 2D hexagonal honeycomb lattice where a layer of Mo atoms is sandwiched between two layers ( the top and bottom layer) of S atoms, with each Mo atom ionically bonded to six S atoms.<sup>1</sup> In order to efficiently simulate the atomic models, the sizes of tip and the monolayer  $MoS_2$  films are scaled down. The rectangular and circular regions with various sizes (80, 100, 120 and 150 Å in diameter or in side length) are defined extending from the center of the films for the nanoindentation simulations, and atoms outside the circular region are fixed as the boundary. A spherical virtual tip with a radius of 3 Å is modeled where there is only repulsive force between tip and monolayer  $MoS_2$  sheets. The tip is loaded along the z-axis, and set as a rigid body to avoid the tip wear. The loading rate was set to 0.2 Å/ps, referring to our previous work.<sup>2</sup>

Large-Scale Atomic/Molecular Massively Parallel Simulator (LAMMPS) was used to perform the AFM nanoindentation. The atomic interactions in the monolayer  $MoS_2$  were determined by the reactive empirical bond-order (REBO) potentials, which has been verified to be more accurate in describing the elastic and mechanical properties of monolayer  $MoS_2$ .<sup>3-6</sup> The interaction between the monolayer  $MoS_2$  and the tip was described by the Lennard–Jones (LJ) potential, which has been demonstrated in our previous works.<sup>2, 4</sup> Before the nanoindentation process, the energy of the system was minimized by the conjugated gradient method, and the isothermal–isobaric (NPT) ensemble controlled by the Nosé-Hoover method was then employed for system relaxation at a temperature of 0.1 K and a pressure of 0.1 bar (the time step is set to 1 fs).



**Figure S5**. The MD simulated loading force-deflection curves, breaking forces  $F_{max}$  and breaking stresses  $\sigma_{max}$  of the rectangular (a, c and e) and circular (b, d and f) monolayer MoS<sub>2</sub> films with various sizes (80, 100, 120 and 150 Å in side length or diameter). The breaking stresses  $\sigma_{max}$  are calculated according to the equation 2 in the paper.

## **References:**

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